

ISC Silicon NPN Power Transistor

2SC3927

DESCRIPTION

- High Collector-Emitter Breakdown Voltage-
 - : V_{(BR)CEO}= 550V(Min)
- High Switching Speed
- High Reliability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

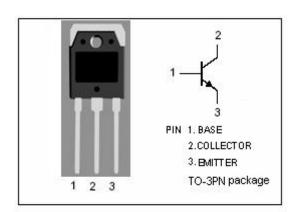


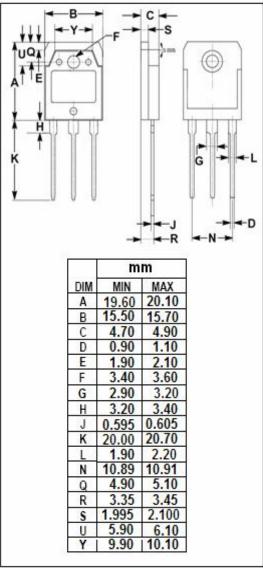
APPLICATIONS

 Designed for switching regulator and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|---|---------------|------------|--|
| V _{CBO} | Collector-Base Voltage | 900 | V | |
| V _{CEO} | Collector-Emitter Voltage | 550 | V | |
| V_{EBO} | Emitter-Base voltage | 7 | V | |
| lc | Collector Current-Continuous | 10 | Α | |
| Ісм | Collector Current-Peak | 15 | Α | |
| lв | Base Current-Continuous | 5 | Α | |
| Pc | Collector Power Dissipation @ T _C =25°C | 120 | W | |
| TJ | Junction Temperature | mperature 150 | | |
| T _{stg} | Storage Temperature Range | -55~150 | $^{\circ}$ | |







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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

| 10-23 C uniess otherwise specified | | | | | | | | | |
|------------------------------------|--------------------------------------|--|-----|------|-----|------|--|--|--|
| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT | | | |
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = 10mA ; I _B = 0 | 550 | | | V | | | |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 5A; I _B = 1A | | | 0.5 | V | | | |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 5A; I _B = 1A | | | 1.2 | V | | | |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 800V ; I _E = 0 | | | 0.1 | mA | | | |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 7V; I _C = 0 | | | 0.1 | mA | | | |
| h _{FE} | DC Current Gain | I _C = 5A ; V _{CE} = 4V | 10 | | 28 | | | | |
| f⊤ | Current-Gain—Bandwidth Product | I _E = -1A ; V _{CE} = 12V | | 6 | | MHz | | | |
| Сов | Output Capacitance | I _E = 0 ; V _{CB} = 10V; f _{test} = 1.0MHz | | 105 | | pF | | | |
| Switching times | | | | | | | | | |
| t _{on} | Turn-on Time | | | | 1.0 | μS | | | |
| t _{stg} | Storage Time | I _C = 5A , I _{B1} = 0.75A; I _{B2} = -1.5A R _L = 50 Ω ; V _{CC} = 250V | | | 5.0 | μS | | | |
| t _f | Fall Time | | | | 0.5 | μS | | | |

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